Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	0	(surface adj channel) near10 (high near k near (insulating or insulator or dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 14:55
S2	49	(surface adj channel) and (high near k near (insulating or insulator or dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 14:55
S3	19	(surface adj channel).ti,ab,clm. and (high near k near (insulating or insulator or dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 14:55
S4	7	(surface adj channel).ti,ab,clm. and (high near k near (insulating or insulator or dielectric)).ti,ab, clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 14:56
S5	8797	(surface adj channel).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 14:56
S6	4612	"surface channel".clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 14:56
S7	439	"surface channel" near10 well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 14:57
S8	86	"surface channel" near10 well and (well near5 source near5 drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 14:57
S9	86	("surface channel" near10 well) and (well near5 source near5 drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 14:57

S10	8	("surface channel" near10 well). clm. and (well near5 source near5 drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 14:57
S11	7	("surface channel" near10 well). clm. and (well near5 source near5 drain).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 14:59
S12	111	li and tingkai	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 14:59
S13	104	(li and tingkai) and sharp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 14:59
S14	7	(li and tingkai) and sharp and (surface near channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:01
S15	0	(li and tingkai) and sharp and (surface near channel) and (high near k)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:02
S16	10	(surface near channel) and (high near k) and sharp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:07
S17	0	((high near k) near (dielectric or insulating or insulator)) near10 (channel near surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:08
S18	1	((high near k) near (dielectric or insulating or insulator)) with (channel near surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:09
S19	0	((high near k) near (dielectric or insulating or insulator)) with (channel adj surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:09

S20	12	((high near k) near (dielectric or insulating or insulator)) and (channel adj surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:09
S21	12	((high near k) near (dielectric or insulating or insulator)) and (channel adj surface) and (gate adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:09
S22	12	((high near k) near (dielectric or insulating or insulator)) and (channel adj surface) and (gate adj electrode) and well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:09
S23	12	((high near k) near (dielectric or insulating or insulator)) and (channel adj surface) and (gate adj electrode) and well and source	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:09
S24	12	((high near k) near (dielectric or insulating or insulator)) and (channel adj surface) and (gate adj electrode) and well and source and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:10
S25	0	(((high near k) near (dielectric or insulating or insulator)) and (channel adj surface) and (gate adj electrode) and well and source and drain).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:10
S26	0	(((high near k) near (dielectric or insulating or insulator)) and (channel adj surface) and (gate adj electrode) and well and source and drain).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:10
S27	12	(((high near k) near (dielectric or insulating or insulator)) and (channel adj surface) and (gate adj electrode) and well and source and drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:10
S28	42	(((high near k) near (dielectric or insulating or insulator)) and (channel near surface) and (gate adj electrode) and well and source and drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:11
S29	6	(((high near k) near (dielectric or insulating or insulator)) and (channel near surface).clm. and (gate adj electrode) and well and source and drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:11

S30	1	(((high near k) near (dielectric or insulating or insulator)).clm. and (channel near surface).clm. and (gate adj electrode) and well and source and drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:13
S31	3	(((high near k) near (dielectric or insulating or insulator)).clm. and (channel near2 surface).clm. and (gate adj electrode) and well and source and drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:13
S32	2	(((high near k) near (dielectric or insulating or insulator)).clm. and (channel near2 surface).clm. and (gate adj electrode).clm. and well and source and drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:13
S33	0	(((high near k) near (dielectric or insulating or insulator)).clm. and (channel near2 surface).clm. and (gate adj electrode).clm. and well. clm. and source and drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:13
S34	0	(((high near k) near (dielectric or insulating or insulator)).clm. and (channel near2 surface).clm. and (gate adj electrode).clm. and well. clm. and source.clm. and drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:13
S35	0	(((high near k) near (dielectric or insulating or insulator)).clm. and (channel near2 surface).clm. and (gate adj electrode).clm. and well. clm. and source.clm. and drain. clm.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:14
S36	0	((((high near k) or (high adj k) or (high-k)) near (dielectric or insulating or insulator)).clm. and (channel near2 surface).clm. and (gate adj electrode).clm. and well. clm. and source.clm. and drain. clm.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:14
S37	0	((((high near k) or (high adj k) or (high-k)) near (dielectric or insulating or insulator)).ti,ab,clm. and (channel near2 surface).clm. and (gate adj electrode).clm. and well.clm. and source.clm. and drain.clm.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:14
S38	0	((((high near k) or (high adj k) or (high-k)) near (dielectric or insulating or insulator)).ti,ab,clm. and (channel near2 surface).ti,ab, clm. and (gate adj electrode).clm. and well.clm. and source.clm. and drain.clm.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:14

S39	0	((((high near k) or (high adj k) or (high-k)) near (dielectric or insulating or insulator)).ti,ab,clm. and (channel near2 surface).ti,ab, clm. and (gate adj electrode).ti,ab, clm. and well.clm. and source.clm. and drain.clm.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:14
S40	1	((((high near k) or (high adj k) or (high-k)) near (dielectric or insulating or insulator)).ti,ab,clm. and (channel near2 surface).ti,ab, clm. and (gate).ti,ab,clm. and well.clm. and source.clm. and drain.clm.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:14
S41	7	((((high near k) or (high adj k) or (high-k)) near (dielectric or insulating or insulator)).ti,ab,clm. and (channel near2 surface).ti,ab, clm. and (gate).ti,ab,clm. and source.clm. and drain.clm.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:15
S42	5	((((high near k) or (high adj k) or (high-k)) near (dielectric or insulating or insulator)).ti,ab,clm. and (channel near2 surface).ti,ab, clm. and (gate adj electrode)).ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:15
S43	2	((((high near k) or (high adj k) or (high-k)) near (dielectric or insulating or insulator)).ti,ab,clm. and (channel near2 surface).clm. and (gate adj electrode)).ti,ab, clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:17
S44	7	(((high near k) or (high adj k) or (high-k)) near (dielectric or insulating or insulator)).ti,ab,clm. and (channel near2 surface).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:18
S45	13	(((high near k) or (high adj k) or (high-k)) near (dielectric or insulating or insulator)).ti,ab,clm. and (channel near2 surface).ti,ab, clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:18
S46	1	(((high near k) or (high adj k) or (high-k)) near (dielectric or insulating or insulator)).ti,ab,clm. and ((channel near2 surface) near10 (source or source/drain or diffusion)).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:20

S47	0	(((high near k) or (high adj k) or (high-k)) near (dielectric or insulating or insulator)).ti,ab,clm. and ((channel near2 surface) near10 (source or source/drain or diffusion) near10 gate).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:20
S48	0	(((high near k) or (high adj k) or (high-k)) near (dielectric or insulating or insulator)).ti,ab,clm. and ((channel near2 surface) near10 (source or source/drain or diffusion) near10 gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:20
S49	1	(((high near k) or (high adj k) or (high-k)) near (dielectric or insulating or insulator)).ti,ab,clm. and ((channel near2 surface) with (source or source/drain or diffusion) with gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:21
S50	2	(((high near k) or (high adj k) or (high-k)) near (dielectric or insulating or insulator)) and ((channel near2 surface) with (source or source/drain or diffusion) with gate with (insulating or dielectric or oxide or insulator))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/09 15:21